

TM200RZ/EZ/GZ-M,-H,-24,-2H

HIGH POWER GENERAL USE
INSULATED TYPE

TM200RZ/EZ/GZ-M,-H,24,-2H



(RZ Type)

- **IT (AV)** Average on-state current **200A**
- **IF (AV)** Average forward current **200A**
- **VRRM** Repetitive peak reverse voltage
..... **400/800/1200/1600V**
- **VDRM** Repetitive peak off-state voltage
..... **400/800/1200/1600V**
- **MIX DOUBLE ARMS**
- **Insulated Type**
- **UL Recognized**

Yellow Card No. E80276 (N)

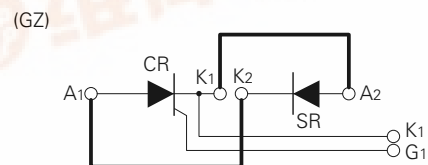
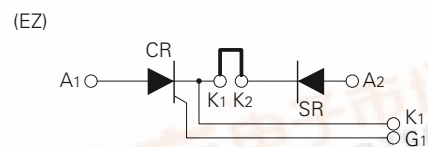
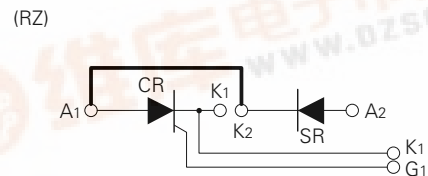
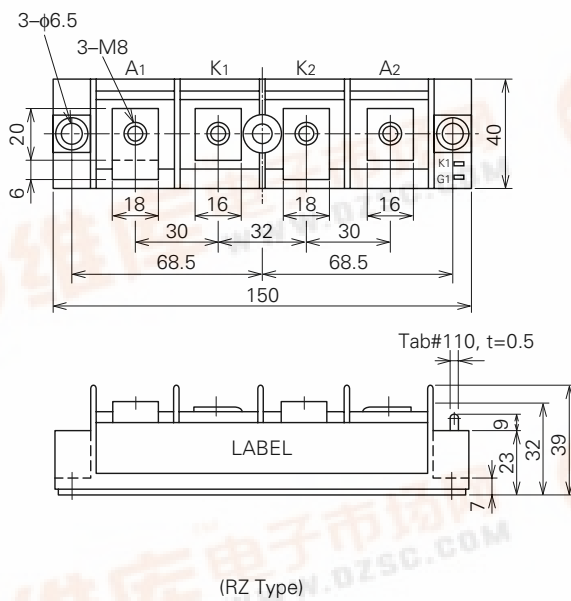
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APPLICATION

DC motor control, NC equipment, AC motor control, contactless switches, electric furnace temperature control, light dimmers

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



(Bold line is connective bar.)

MITSUBISHI THYRISTOR MODULES

TM200RZ/EZ/GZ-M,-H,-24,-2H

MEDIUM POWER GENERAL USE
INSULATED TYPE

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Voltage class				Unit
		M	H	24	H	
VRRM	Repetitive peak reverse voltage	400	800	1200	1600	V
VRSM	Non-repetitive peak reverse voltage	480	960	1350	1700	V
VR (DC)	DC reverse voltage	320	640	960	1280	V
VDRM	Repetitive peak off-state voltage	400	800	1200	1600	V
VDSM	Non-repetitive peak off-state voltage	480	960	1350	1700	V
VD (DC)	DC off-state voltage	320	640	960	1280	V

Symbol	Parameter	Conditions	Ratings	Unit
IT (RMS), IF (RMS)	RMS current		310	A
IT (AV), IF (AV)	Average current	Single-phase, half-wave 180° conduction, Tc=67°C	200	A
ITSM, IFSM	Surge (non-repetitive) current	One half cycle at 60Hz, peak value	4000	A
I ² t	I ² t for fusing	Value for one cycle of surge current	6.7 × 10 ⁴	A ² s
di/dt	Critical rate of rise of on-state current	VD=1/2VDRM, IG=1.0A, Tj=125°C	100	A/μs
PGM	Peak gate power dissipation		10	W
PG (AV)	Average gate power dissipation		3.0	W
VFGM	Peak gate forward voltage		10	V
VRGM	Peak gate reverse voltage		5.0	V
IFGM	Peak gate forward current		4.0	A
Tj	Junction temperature		-40~125	°C
Tstg	Storage temperature		-40~125	°C
Viso	Isolation voltage	Charged part to case	2500	V
—	Mounting torque	Main terminal screw M8	8.83~10.8	N·m
			90~110	kg·cm
		Mounting screw M6	1.96~3.92	N·m
			20~40	kg·cm
—	Weight	Typical value	300	g

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IRRM	Repetitive peak reverse current	Tj=125°C, VRRM applied	—	—	30	mA
IDRM	Repetitive peak off-state current	Tj=125°C, VDRM applied	—	—	30	mA
VTM, VFM	Forward voltage	Tj=125°C, ITM=IFM=600A, instantaneous meas.	—	—	1.35	V
dv/dt	Critical rate of rise of off-state voltage	Tj=125°C, VD=2/3VDRM	500	—	—	V/μs
VGT	Gate trigger voltage	Tj=25°C, VD=6V, RL=2Ω	—	—	3.0	V
VGD	Gate non-trigger voltage	Tj=125°C, VD=1/2VDRM	0.25	—	—	V
IGT	Gate trigger current	Tj=25°C, VD=6V, RL=2Ω	15	—	100	mA
Rth (j-c)	Thermal resistance	Junction to case (per 1/2 module)	—	—	0.2	°C/W
Rth (c-f)	Contact thermal resistance	Case to fin, conductive grease applied (per 1/2 module)	—	—	0.1	°C/W
—	Insulation resistance	Measured with a 500V megohmmeter between main terminal and case	10	—	—	MΩ

Note: Items of the above table applies to the Thyristor part and the Diode part as circled in the following tables.

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MAXIMUM RATINGS

Item	VRRM	VRSM	VR (DC)	VDRM	VD SM	VD (DC)	IT (RMS)	IT (AV)	ITSM	I ² t	di/dt
							IF (RMS)	IF (AV)	IFSM		
Thyristor	○	○	○	○	○	○	○	○	○	○	○
Diode	○	○	○	—	—	—	○	○	○	○	—

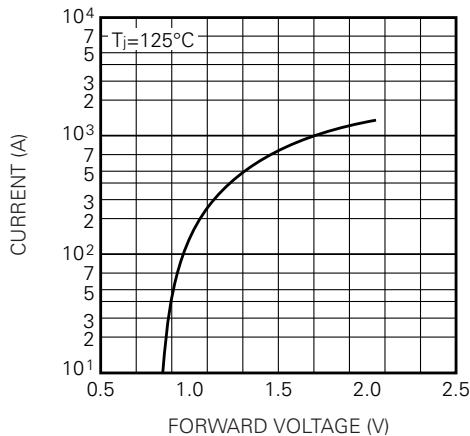
Item	PGM	PG (AV)	VFGM	IFGM	T _j	T _{stg}
Thyristor	○	○	○	○	○	○
Diode	—	—	—	—	○	○

ELECTRICAL CHARACTERISTICS

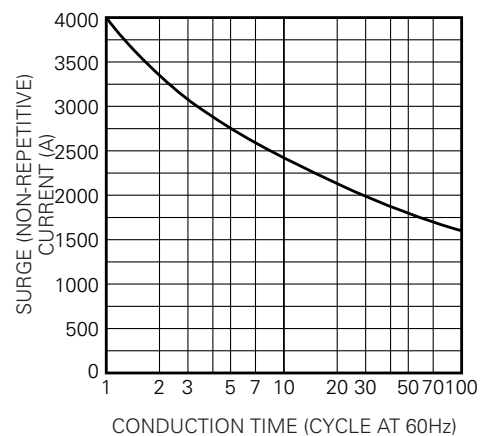
Item	IRR M	IDRM	V _{TM}	dv/dt	V _{GT}	V _{GD}	I _{GT}	R _{th (j-c)}	R _{th (c-f)}
			V _{FM}						
Thyristor	○	○	○	○	○	○	○	○	○
Diode	○	—	○	—	—	—	—	○	○

PERFORMANCE CURVES

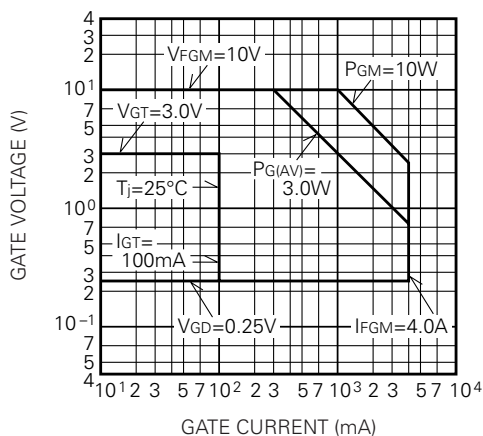
MAXIMUM FORWARD CHARACTERISTIC



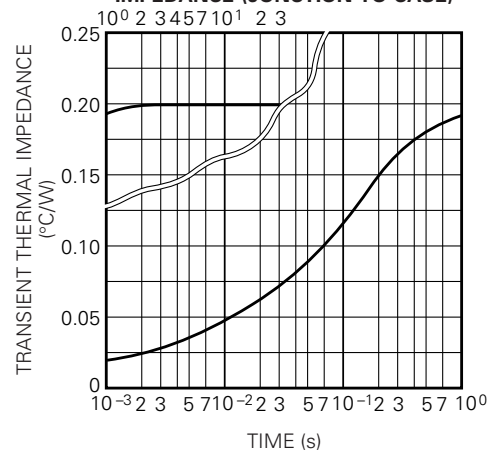
RATED SURGE (NON-REPETITIVE) CURRENT



GATE CHARACTERISTICS



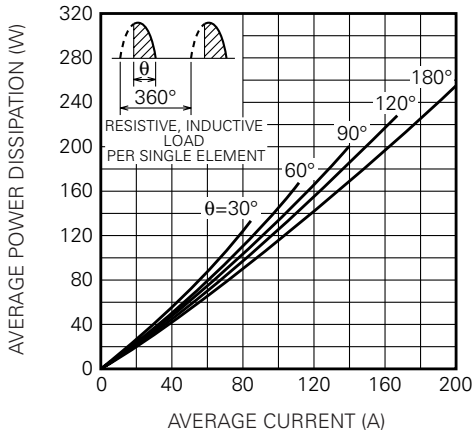
MAXIMUM TRANSIENT THERMAL IMPEDANCE (JUNCTION TO CASE)



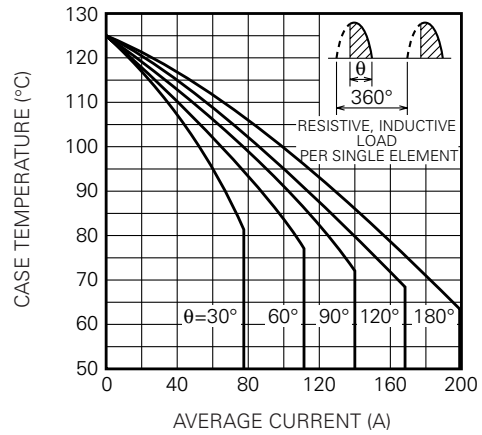
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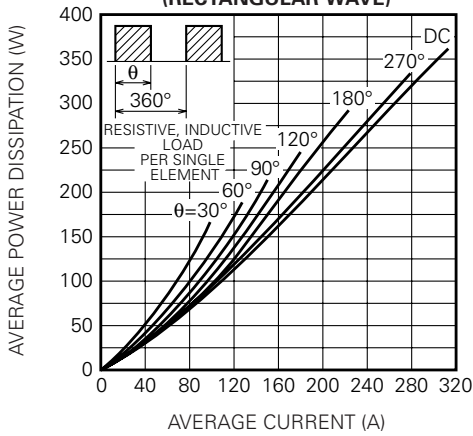
MAXIMUM AVERAGE POWER DISSIPATION (SINGLE PHASE HALF WAVE)



LIMITING VALUE OF THE AVERAGE CURRENT (SINGLE PHASE HALF WAVE)



MAXIMUM AVERAGE POWER DISSIPATION (RECTANGULAR WAVE)



LIMITING VALUE OF THE AVERAGE CURRENT (RECTANGULAR WAVE)

